

N-Channel 600V(D-S) Super Junction Power MOSFET

PRODUCT SUMMARY		
V _{DS} (V) at T _J max.	600	
R _{DS(on)} at 25 °C (Ω)	V _{GS} = 10 V	0.056
Q _g max. (nC)	228	
Q _{gs} (nC)	32	
Q _{gd} (nC)	62	
Configuration	Single	

FEATURES

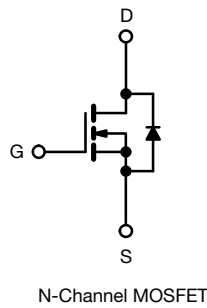
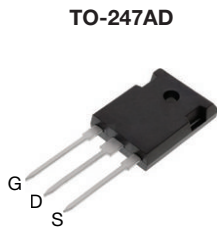
- Fast body diode MOSFET using E series technology
- Reduced t_{rr}, Q_{rr}, and I_{RRM}
- Low figure-of-merit (FOM) R_{on} x Q_g
- Low input capacitance (C_{iss})
- Increased robustness due to low Q_{rr}
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Telecommunications
 - Server and telecom power supplies
- Lighting
 - High-intensity lighting (HID)
 - Light emitting diodes (LEDs)
- Consumer and computing
 - ATX power supplies
- Industrial
 - Welding
 - Battery chargers
- Renewable energy
 - Solar (PV inverters)
- Switching mode power supplies (SMPS)
 - Applications using the following topologies
 - LLC
 - Phase shifted bridge (ZVS)
 - 3-level inverter
 - AC/DC bridge




ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	600	V
Gate-Source Voltage	V _{GS}	± 30	
Continuous Drain Current (T _J = 150 °C)	V _{GS} at 10 V	T _C = 25 °C	A
		T _C = 100 °C	
Pulsed Drain Current ^a	I _{DM}	138	
Linear Derating Factor		3	W/°C
Single Pulse Avalanche Energy ^b	E _{AS}	1500	mJ
Maximum Power Dissipation	P _D	379	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Drain-Source Voltage Slope	dV/dt	T _J = 125 °C	V/ns
Reverse Diode dV/dt ^d		50	
Soldering Recommendations (Peak Temperature) ^c	for 10 s	300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- V_{DD} = 50 V, starting T_J = 25 °C, L = 73.5 mH, R_g = 25 Ω, I_{AS} = 6.4 A
- 1.6 mm from case
- I_{SD} ≤ I_D, dI/dt = 500 A/μs, starting T_J = 25 °C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.33	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$		-	-	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
		$V_{GS} = \pm 30\text{ V}$		-	-	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	μA
		$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 24\text{ A}$	-	0.056	-	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 30\text{ V}, I_D = 24\text{ A}$		-	17	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$		-	5000	-	pF
Output Capacitance	C_{oss}			-	220	-	
Reverse Transfer Capacitance	C_{rss}			-	7	-	
Effective Output Capacitance, Energy Related ^a	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$		-	172	-	pF
Effective Output Capacitance, Time Related ^b	$C_{o(tr)}$			-	634	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 24\text{ A}, V_{DS} = 480\text{ V}$	-	152	228	nC
Gate-Source Charge	Q_{gs}			-	32	-	
Gate-Drain Charge	Q_{gd}			-	62	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 480\text{ V}, I_D = 24\text{ A}, V_{GS} = 10\text{ V}, R_g = 4.4\text{ }\Omega$		-	30	60	ns
Rise Time	t_r			-	56	84	
Turn-Off Delay Time	$t_{d(off)}$			-	91	137	
Fall Time	t_f			-	56	84	
Gate Input Resistance	R_g	$f = 1\text{ MHz}, \text{open drain}$		0.2	0.46	1.0	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	47	A	
Pulsed Diode Forward Current	I_{SM}		-	-	138		
Diode Forward Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 24\text{ A}, V_{GS} = 0\text{ V}$		-	0.9	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 24\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 400\text{ V}$		-	199	398	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	1.4	2.8	μC
Reverse Recovery Current	I_{RRM}			-	13.2	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}
- b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

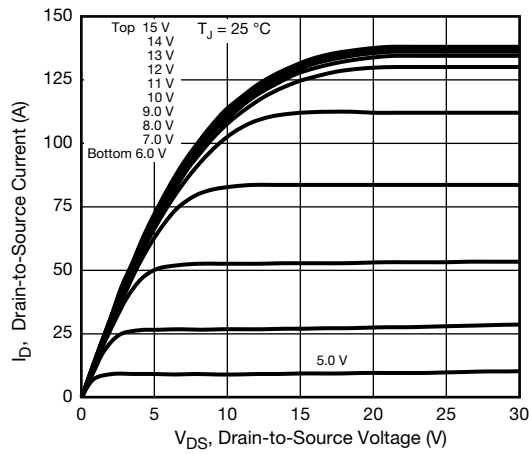


Fig. 1 - Typical Output Characteristics

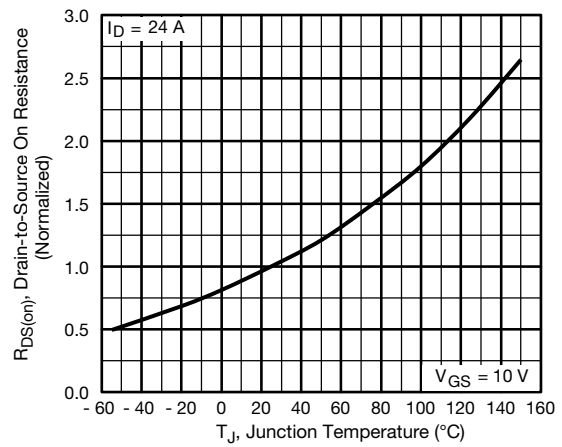


Fig. 4 - Normalized On-Resistance vs. Temperature

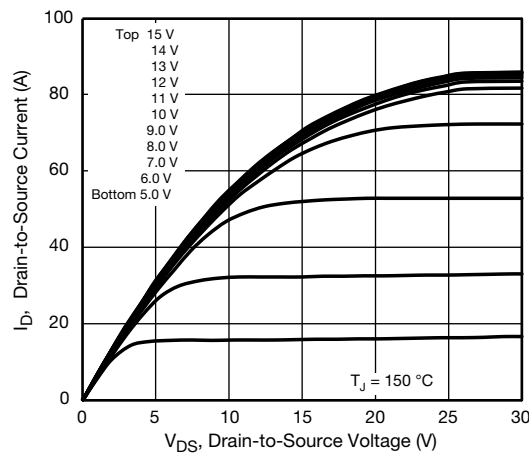


Fig. 2 - Typical Output Characteristics

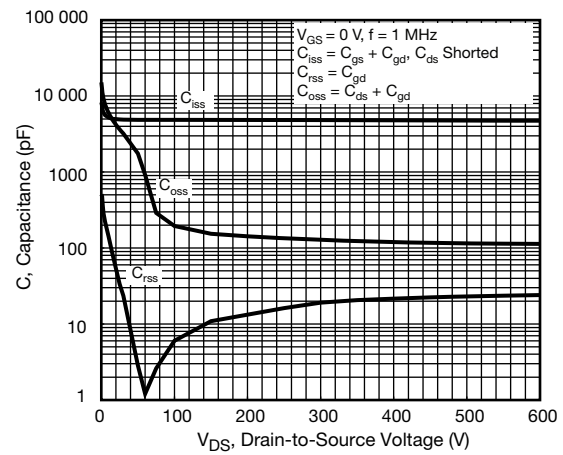


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

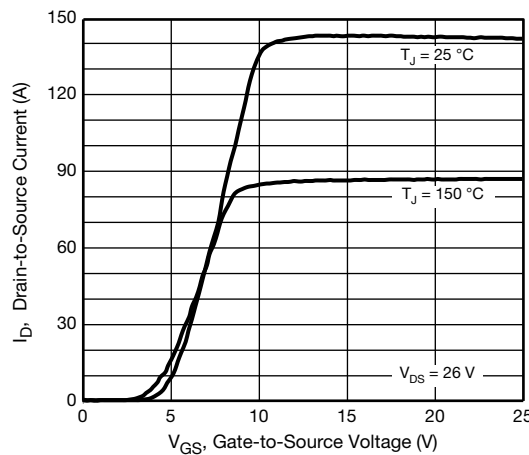


Fig. 3 - Typical Transfer Characteristics

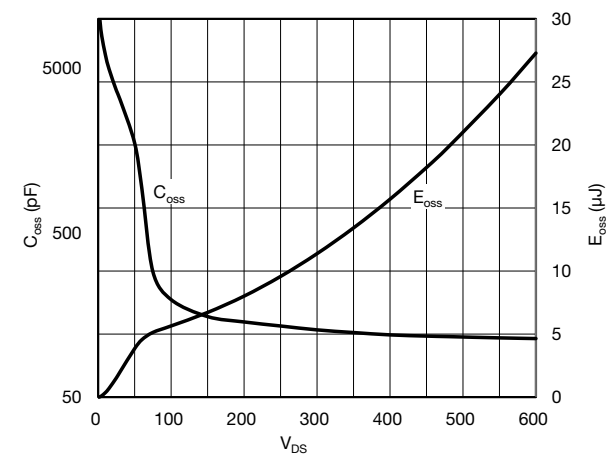


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

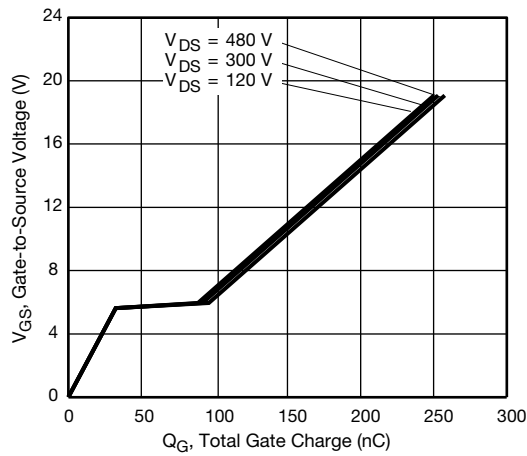


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

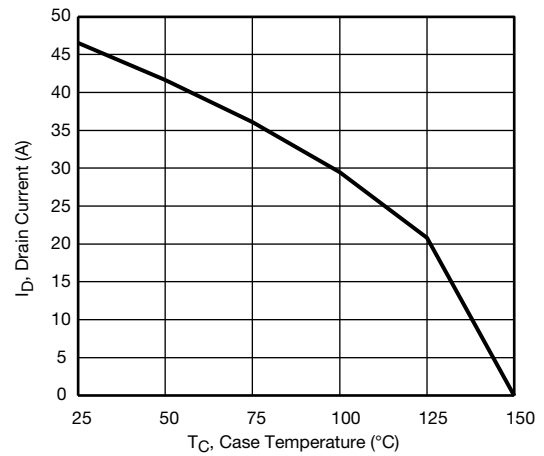


Fig. 10 - Maximum Drain Current vs. Case Temperature

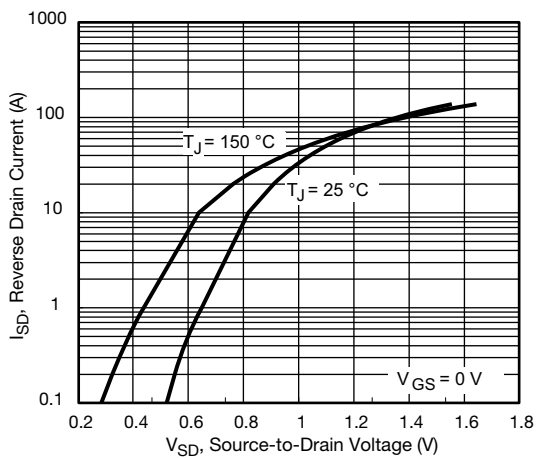


Fig. 8 - Typical Source-Drain Diode Forward Voltage

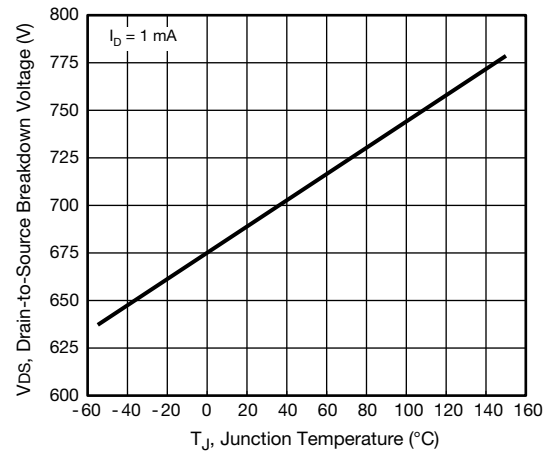


Fig. 11 - Temperature vs. Drain-to-Source Voltage

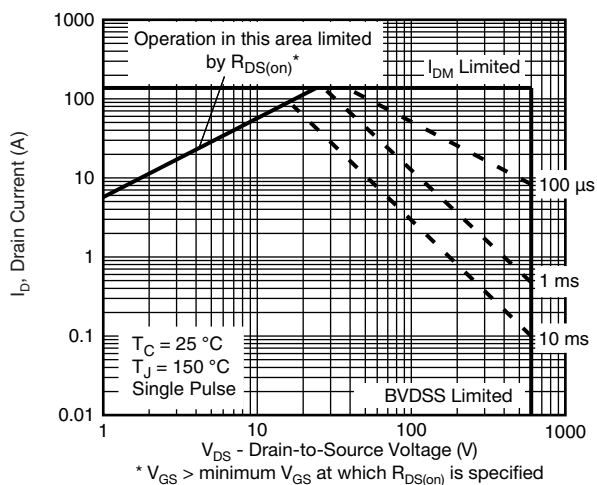


Fig. 9 - Maximum Safe Operating Area

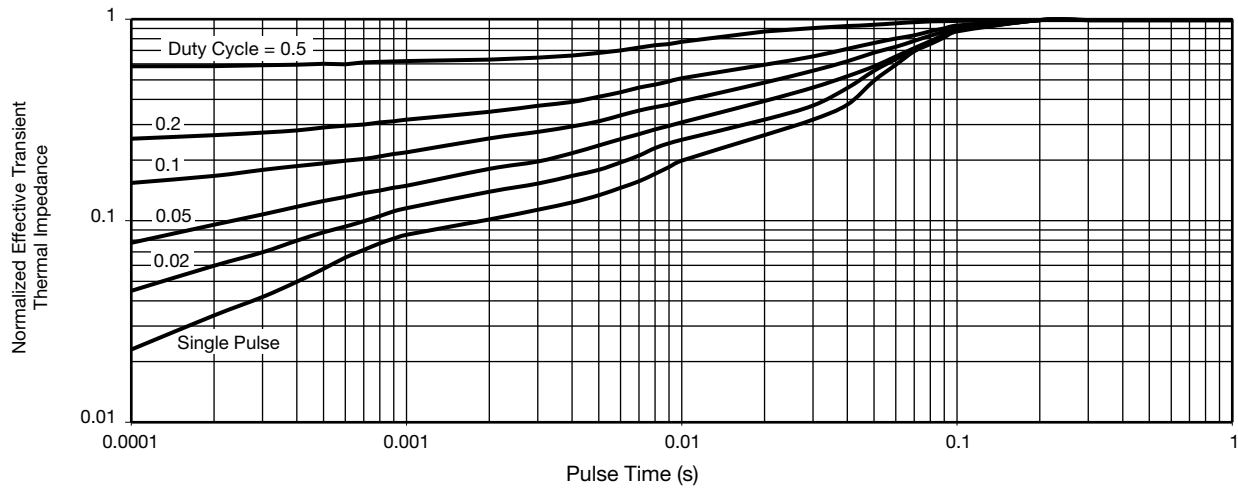


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

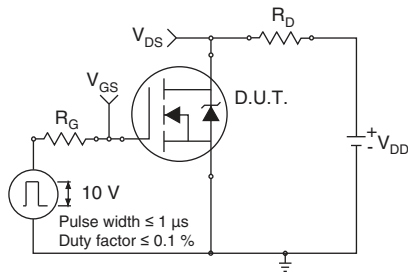


Fig. 13 - Switching Time Test Circuit

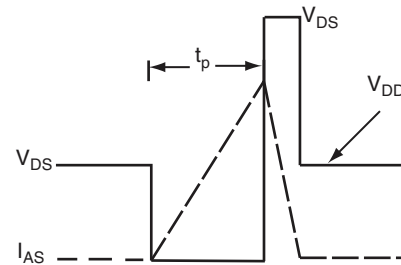


Fig. 16 - Unclamped Inductive Waveforms

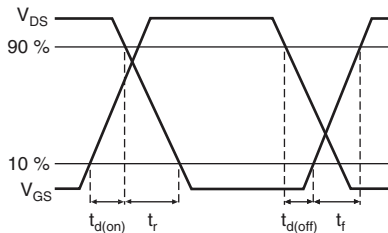


Fig. 14 - Switching Time Waveforms

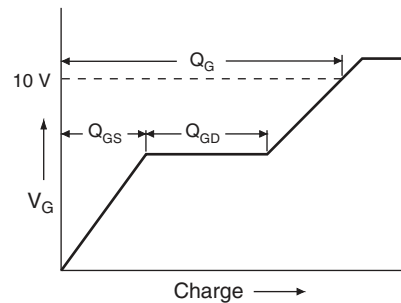


Fig. 17 - Basic Gate Charge Waveform

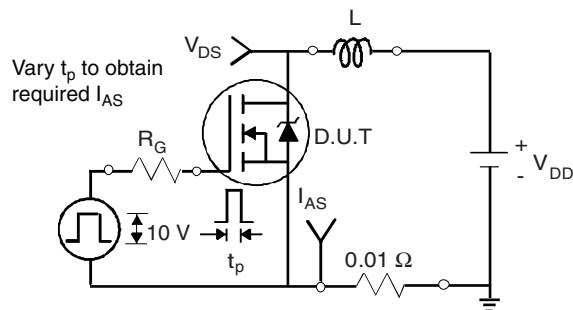


Fig. 15 - Unclamped Inductive Test Circuit

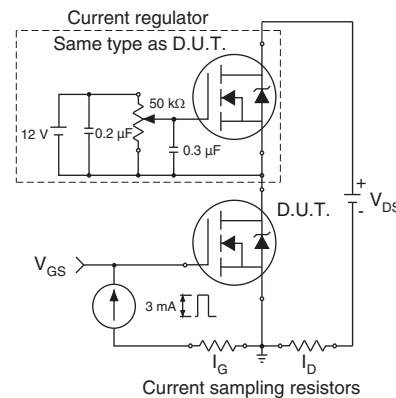
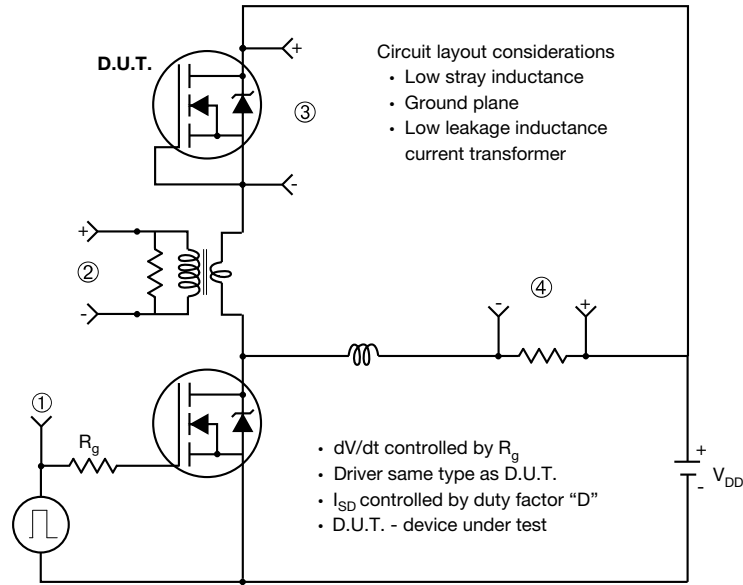


Fig. 18 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 18 - For N-Channel

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